

PJ32 Process

Silicon Junction Field-Effect Transistor

• General Purpose Amplifier

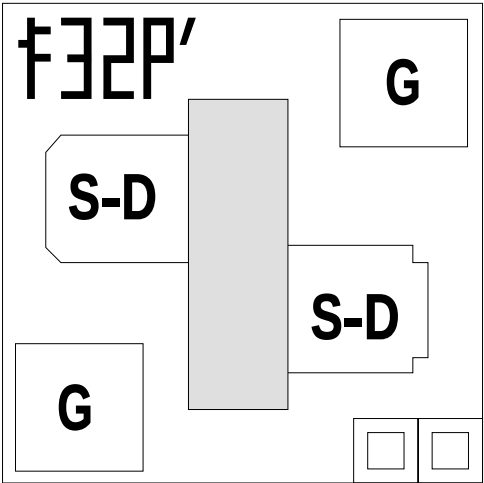
Absolute maximum ratings at TA = 25 °C

Gate Current, Ig	10 mA
Operating Junction Temperature, Tj	+150°C
Storage Temperature, Ts	– 65°C to +175°C

Devices in this Databook based on the PJ32 Process.

Datasheet

2N5020, 2N5021
2N5460, 2N5461
2N5462



Die Size = 0.018" X 0.018"
All Bond Pads = 0.004" Sq.
Substrate is also Gate.

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At 25°C free air temperature:		PJ32 Process					
		Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	V _{(BR)GSS}	30	50		V	I _G = 1 μA, V _{DS} = Ø	
Reverse Gate Leakage Current	I _{GSS}		1	2	nA	V _{GS} = 15V, V _{DS} = Ø	
Drain Saturation Current (Pulsed)	I _{DSS}	– 1		– 15	mA	V _{DS} = – 15V, V _{GS} = Ø	
Gate Source Cutoff Voltage	V _{GS(OFF)}	0.5		7	V	V _{DS} = – 15V, I _D = 1 nA	
Dynamic Electrical Characteristics							
Forward Transconductance	g _{fs}		2.5		mS	V _{DS} = – 15V, V _{GS} = Ø	f = 1 kHz
Input Capacitance	C _{iss}		3.2		pF	V _{DS} = Ø, V _{GS} = 10	f = 1 MHz
Feedback Capacitance	C _{rss}		1.7		pF	V _{DS} = Ø, V _{GS} = 10	f = 1 MHz
Equivalent Noise Voltage	e _N		10		nV/√HZ	V _{DS} = 10V, V _{GS} = Ø	f = 1 Hz

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